

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A hard film formed of a material containing a $(M_{1-x}Si_x)(C_{1-d}N_d)$ compound, wherein M is at least one of elements in groups 3A, 4A, 5A and 6A and Al, $0.45 \leq x \leq 0.98$ and $0 \leq d \leq 1$, where x, 1-x, d and 1-d are atomic ratios of Si, M, N and C, respectively, and the hard film has a combination of lubricity, low friction coefficient, wear resistance, small specific abrasion loss, and adhesion to a substrate in an aqueous environment.

Claim 2 (Currently Amended): The hard film according to claim 1, wherein the material further contains O in an atomic ~~ratio~~ ratio in the range of 0.01 to 0.2.

Claim 3 (Original): The hard film according to claim 1, wherein diffraction peak half width of a (111)-plane of the $(M_{1-x}Si_x)(C_{1-d}N_d)$ compound measured by x-ray diffraction is 1.5° or above.

Claim 4 (Original): The hard film according to claim 1, wherein the element M is Cr, Ti or Zr.

Claim 5 (Withdrawn): A laminated hard film formed by alternately superposing the hard film according to claim 1, and a hard film formed of a material containing a $(M_{1-x}Si_x)(C_{1-d}N_d)$ compound at a stacking period in the range of 1 to 1000 nm,

wherein M is at least one of elements of groups 3A, 4A, 5A and 6A and Al, $0 \leq x \leq 0.45$ and $0 \leq d \leq 1$, where x, 1-x, d and 1-d are atomic ratios of Si, M, N and C, respectively.

Claim 6 (Withdrawn): A hard film formed of a material containing a $(M_{1-x}Si_x)$
 $(C_{1-d}N_d)$ compound on a substrate,

wherein M is at least one of elements of groups 3A, 4A, 5A and 6A and Al, the most inner portion of the hard film contiguous with the substrate meets $0 \leq x \leq 0.45$ and $0 \leq d \leq 1$, where x, 1-x, d and 1-d are atomic ratios of Si, M, N and C, respectively, the most outer portion of the hard film meets $0.45 \leq x \leq 0.98$ and $0 \leq d \leq 1$, where x, 1-x, d and 1-d are atomic ratios of Si, M, N and C, respectively, and outer portion of the hard film has higher Si atomic ratio x.